

IN THE ABSTRACT OF DISCLOSURE (clean version)

The present invention relates to a thermal processing method includes a first thermal processing step that carries out thermal processing steps using a plurality of first substrates, wherein thin films are formed on surfaces of the plurality of first substrates by means of less consumption of the process gas than on surfaces of production substrates. Then, a second thermal processing step carries out thermal processing steps by using a plurality of second substrates, wherein thin films are formed on surfaces of the plurality of second substrates by means of more consumption of the process gas than on the surfaces of the plurality of first substrates, and wherein heating units are respectively adjusted to respective temperature set values set during the previous step. Then, a third thermal processing step carries out thermal processing steps by using production substrates as the plurality of substrates, wherein the plurality of heating units are respectively adjusted to the respective temperature set values corrected during the previous step.